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鴻山電子股份有限公司 HOSUNLINK ELECTRON CO., LTD.

台北縣三重市重陽路三段192之4號8樓

8F., NO. 192-4, SEC. 3, CHONGYANG RD., SANCHONG CITY, TAIPEI COUNTY 241, TAIWAN (R. O. C.)

以下測試樣品係由客户送樣,且由客户聲稱並經客户確認如下 (The following samples was/were submitted and identified by/on behalf of the client as):

樣品名稱(Sample Description) 樣品型號(Style/Item No.)

收件日期(Sample Receiving Date)

測試期間(Testing Period)

: CRYSTAL DIP (CYLINDRICAL PACKAGE)

: H-206 / H-308 / H-309 (2\*6 / 3\*8 / 3\*9:MHZ)

: 2008/4/30

: 2008/4/30 TO 2008/5/8

測試結果(Test Results)

: 請見下一頁 (Please refer to next pages).

Chenyu Kung / Operation Manager Signed for and on behalf of SGS TAIWAN LTD.

Chemical Laboratory - Taipei



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#### 測試結果(Test Results)

測試部位(PART NAME) NO.1 : 整體混測 (MIXED ALL PARTS)

測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測 極限値 (MDL)	結果 (Result) NO.1
鎘 / Cadmium (Cd)	mg/kg	參考IEC 62321/2nd CDV (111/95/CDV) 方法,用感應藕合電漿原子發射光譜儀 (ICP-AES) 檢測鎬含量./ With reference to IEC 62321/2nd CDV (111/95/CDV). Determination of Cadmium by ICP-AES.	2	n.d.
鉛 / Lead (Pb)	mg/kg	參考 IEC 62321/2nd CDV (111/95/CDV) 方法,用感應藕合電漿原子發射光譜儀 (ICP-AES)檢測鉛含量./With reference to IEC 62321/2nd CDV (111/95/CDV). Determination of Lead by ICP-AES.	2	23
汞 / Mercury (Hg)	mg/kg	參考IEC 62321/2nd CDV (111/95/CDV) 方法,用感應藕合電漿原子發射光譜儀 (ICP-AES) 檢測汞含量./ With reference to IEC 62321/2nd CDV (111/95/CDV). Determination of Mercury by ICP-AES.	2	n.d.
六價鉻 / Hexavalent Chromium Cr(VI) by alkaline extraction	mg/kg	針對非金屬材質之樣品,參考IEC 62321/2nd CDV (111/95/CDV) 方法檢測, 用UV-VIS檢測六價鉻含量./ With reference to IEC 62321/2nd CDV (111/95/CDV). Determination of Hexavalent Chromium for nonmetallic samples by UV-Vis Spectrometry.	2	n.d.



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測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測 極限値 (MDL)	結果 (Result) NO.1
多溴聯苯總和 / Sum of PBBs			-	n.d.
一溴聯苯 / Monobromobiphenyl			5	n.d.
二溴聯苯 / Dibromobiphenyl			5	n.d.
三溴聯苯 / Tribromobiphenyl			5	n.d.
四溴聯苯 / Tetrabromobiphenyl			5	n.d.
五溴聯苯 / Pentabromobiphenyl			5	n.d.
六溴聯苯 / Hexabromobiphenyl			5	n.d.
七溴聯苯 / Heptabromobiphenyl	]		5	n.d.
八溴聯苯 / Octabromobiphenyl			5	n.d.
九溴聯苯 / Nonabromobiphenyl			5	n.d.
十溴聯苯 / Decabromobiphenyl		參考IEC 62321/2nd CDV (111/95/CDV) 方法,以氣相層析儀/質譜儀檢測多溴聯 苯和多溴聯苯醚含量./With reference to IEC 62321/2nd CDV (111/95/CDV). Determination of PBB and PBDE by GC/MS.	5	n.d.
多溴聯苯醚總和(一至九溴)/ Sum of			-	n.d.
PBDEs (Mono to Nona) (Note 4)	mg/kg			
一溴聯苯醚 / Monobromodiphenyl ether			5	n.d.
二溴聯苯醚 / Dibromodiphenyl ether			5	n.d.
三溴聯苯醚 / Tribromodiphenyl ether			5	n.d.
四溴聯苯醚 / Tetrabromodiphenyl ether			5	n.d.
五溴聯苯醚 / Pentabromodiphenyl ether			5	n.d.
六溴聯苯醚 / Hexabromodiphenyl ether			5	n.d.
七溴聯苯醚 / Heptabromodiphenyl ether			5	n.d.
八溴聯苯醚 / Octabromodiphenyl ether			5	n.d.
九溴聯苯醚 / Nonabromodiphenyl ether			5	n.d.
十溴聯苯醚 / Decabromodiphenyl ether			5	n.d.
多溴聯苯醚總和(一至十溴)/ Sum of			-	n.d.
PBDEs (Mono to Deca)				



## 測試報告

# **Test Report**

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鴻山電子股份有限公司

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8F., NO. 192-4, SEC. 3, CHONGYANG RD., SANCHONG CITY, TAIPEI COUNTY 241, TAIWAN

(R. O. C.)

測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測 極限値 (MDL)	結果 (Result) NO.1
鹵素 / Halogen		参考BS EN 14582:2007, 以離子層析儀 分析氟, 氣, 溴, 碘含量. / With reference to BS EN 14582:2007. Analysis was performed by IC method for F, Cl, Br, I content.		
鹵素(氟)/ Halogen-Fluorine (F) (CAS No.: 007782-41-4)	mg/kg	参考BS EN 14582:2007, 以離子層析儀 分析氣含量. / With reference to BS EN 14582:2007. Analysis was performed by IC method for Fluorine content.	50	n.d.
鹵素(氣)/ Halogen-Chlorine (C1) (CAS No.: 007782-50-5)	mg/kg	参考BS EN 14582:2007, 以離子層析儀 分析氣含量. / With reference to BS EN 14582:2007. Analysis was performed by IC method for Chlorine content.	50	n.d.
鹵素(溴)/ Halogen-Bromine (Br) (CAS No.: 007726-95-6)	mg/kg	参考BS EN 14582:2007, 以離子層析儀 分析溴含量. / With reference to BS EN 14582:2007. Analysis was performed by IC method for Bromine content.	50	n.d.
鹵素(碘)/ Halogen-Iodine (I) (CAS No.: 007553-56-2)	mg/kg	参考BS EN 14582:2007, 以離子層析儀 分析碘含量. / With reference to BS EN 14582:2007. Analysis was performed by IC method for Iodine content.	50	n.d.

#### 備註(Note):

- 1. mg/kg = ppm
- 2. n.d. = Not Detected (未檢出)
- 3. MDL = Method Detection Limit (方法偵測極限值)
- 4. 根據2005年10月13日歐盟會議公佈2005/717/EC,修訂2002/95/EC內容,通過解除高分子材質中十溴聯苯醚之使用限制. (According to 2005/717/EC DecaBDE is exempt.)
- 5. "-" = Not Regulated (無規格值)
- 6. "---" = Not Conducted (未測項目)
- 7. 樣品的測試是基於申請人要求混合測試,報告中的混合測試結果不代表其中個别單一材質的含量. (The samples was/were analyzed on behalf of the applicant as mixing sample in one testing. The above results was/were only given as the informality value)

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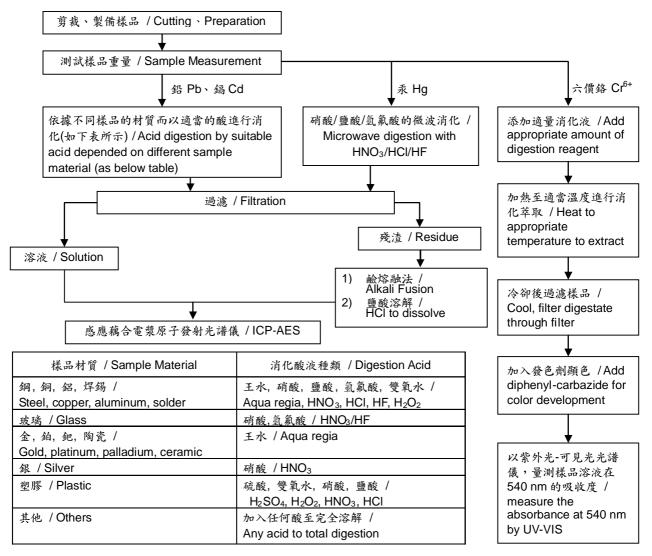
鴻山電子股份有限公司

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- 1) 根據以下的流程圖之條件,樣品已完全溶解。( 六價鉻測試方法除外 ) / These samples were dissolved totally by pre-conditioning method according to below flow chart. (Cr<sup>6+</sup> test method excluded )
- 2) 測試人員:楊登偉 / Name of the person who made measurement: Climbgreat Yang
- 3) 測試負責人: 張啓興 / Name of the person in charge of measurement: Troy Chang



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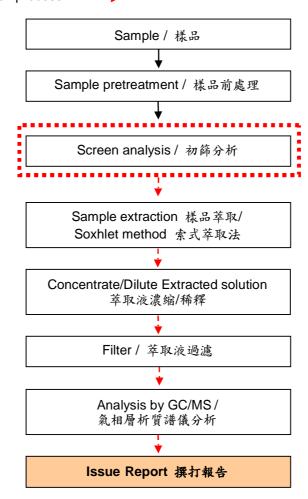
### 多溴聯苯/多溴聯苯醚分析流程圖 / PBB/PBDE analytical FLOW CHART

- 1) 測試人員: 翁賜彬 / Name of the person who made measurement: Tin Lan
- 2) 測試負責人: 陳新智 / Name of the person in charge of measurement: Shinjyh Chen

初次測試程序 / First testing process ———▶

選擇性篩檢程序 / Optional screen process ......

確認程序 / Confirmation process \_ . \_ ▶

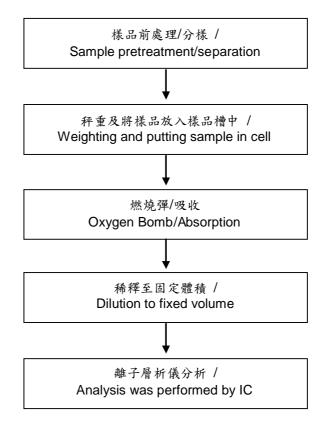




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- 1) 測試人員:藍雅婷 / Name of the person who made measurement: Tin Lan
- 2) 測試負責人:張啓興 / Name of the person in charge of measurement: Troy Chang





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\*\* 報告結尾 \*\*